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**PATENT**  
Attorney Docket No.: ASC-025DV1

**Particulars of prior application:**

**Serial No.: 09/928,126  
Filing Date: August 10, 2001  
Examiner: C. Thompson of Art Unit 2813  
Status: Allowed**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

APPLICANT:	Cheng et al.		
SERIAL NO.:	Not yet assigned	GROUP NO.:	Not yet assigned
FILING DATE:	Herewith	EXAMINER:	Not yet assigned
TITLE:	PROCESS FOR PRODUCING SEMICONDUCTOR ARTICLE USING GRADED EPITAXIAL GROWTH		

BOX PATENT APPLICATION  
Commissioner for Patents  
Washington, D.C. 20231

**PRELIMINARY AMENDMENT**

Sir:

Please enter the following preliminary amendment before beginning examination of the above-identified divisional patent application.

**AMENDMENTS**

**To the Title Page:**

Please rewrite the title as --PROCESS FOR PRODUCING SEMICONDUCTOR ARTICLE USING GRADED EPITAXIAL GROWTH--.

**To the Specification:**

On page 1, after the heading "PRIORITY INFORMATION" rewrite the paragraph on lines 5–6 as: